

## Description

The LBSS84-HXY uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

 $V_{DS} = -50V, I_{D} = -0.1A$ 

 $R_{DS(ON)}$  <5  $\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)}$  <6  $\Omega$  @  $V_{GS}$ =-4.5V



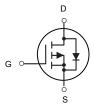
SOT-23

#### **Application**

Power switching application

Hard switched and high frequency circuits

DC-DC converter



P-Channel MOSFET

#### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
LBSS84-HXY	SOT-23	PD	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	-50	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	-0.1	Α
Pulsed Drain Current	I <sub>DM</sub>	-0.5	Α
Maximum Power Dissipation	P <sub>D</sub>	0.35	W
Operating Junction and Storage Temperature Range	$T_{J}$ , $T_{STG}$	-55 To 150	$^{\circ}$
Thermal Resistance ,Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	62.5	°C/W



## **Electrical Characteristics (Ta=25℃ unless otherwise specified)**

Symbol	Parameter	Test conditions	Min	Тур	Max	Unit
Static	Static					
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	V <sub>GS</sub> =0, I <sub>D</sub> =250μA	-50			V
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.8		-2.0	V
I <sub>GSS</sub>	Gate-body leakage current	V <sub>DS</sub> =0, V <sub>GS</sub> =±10V			±10	μA
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V			-10	μA
IDSS		V <sub>DS</sub> =-40V, V <sub>GS</sub> =0V			-100	nA
D	Drain-source on-resistance <sup>a</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-0.13A		2	5	Ω
R <sub>DS(on)</sub>		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.13A		2.5	6	Ω
<b>g</b> FS	Forward transconductance <sup>a</sup>	V <sub>DS</sub> =-25V, I <sub>D</sub> =-0.13A	50			mS
$V_{SD}$	Diode forward voltage	I <sub>S</sub> =-0.13A,V <sub>GS</sub> =0V			-1.0	V
Dynamic						
C <sub>iss</sub>	Input capacitance			25		
Coss	Output capacitance	$V_{DS}$ =-25V, $V_{GS}$ =0V, f=1MHz		15		pF
C <sub>rss</sub>	Reverse transfer capacitance <sup>b</sup>			3.5		
Switching	Switching <sup>b</sup>					
t <sub>d(on)</sub>	Turn-on delay time			16.7		
t <sub>r</sub>	Rise time	V <sub>GS</sub> =-10V,V <sub>DS</sub> =-15V		8.6		nS
t <sub>d(off)</sub>	Turn-off delay time	$I_D$ =-200mA, $R_{GEN}$ =25 $\Omega$		17.9		113
t <sub>f</sub>	Fall time			5.3		

Notes:

a. Pulse Test : Pulse width≤300µs, duty cycle ≤2%. b. Guaranteed by design, not subject to producting.



## **TypicalCharacteristics**

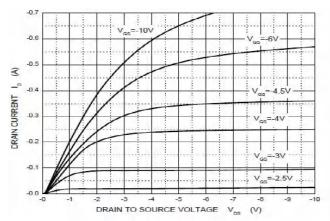


Figure 1. Output Characteristics

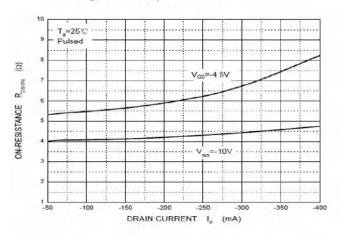


Figure3. Drain-Source on Resistance

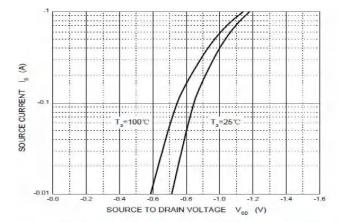


Figure 5. Diode Forward Voltage vs. current

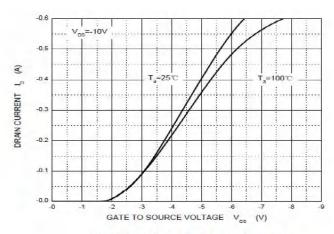


Figure 2. Transfer Characteristics

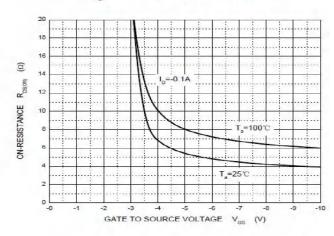


Figure 4. Drain-Source on Resistance

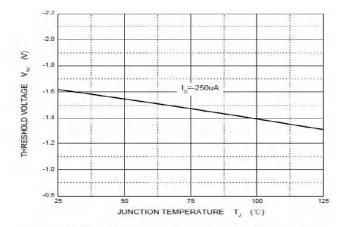
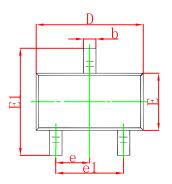
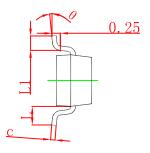


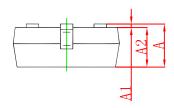
Figure 6. Gate Threshold vs. Junction Temperature



# **SOT-23 Package Outline Dimensions**

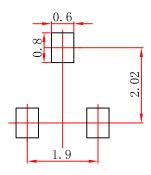






Cumbal	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



#### **Attention**

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.

  HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by HXY MOS manufacturer:

Other Similar products are found below:

614233C 648584F MCH3443-TL-E MCH6422-TL-E NTNS3A92PZT5G IRFD120 IRFF430 JANTX2N5237 2N7000 AOD464
2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C
IPS70R2K0CEAKMA1 BSF024N03LT3 G PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7
EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMC2700UDMQ-7
DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1
DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 IPSA70R950CEAKMA1 IPSA70R2K0CEAKMA1 STU5N65M6
C3M0021120D DMN6022SSD-13